

THE DEVELOPMENT OF THE PERIODICAL DISTRIBUTION OF POINT DEFECTS IN BINARY SEMICONDUCTORS

V. V. Mykhaylovskyy

An instability of the stationary uniform distribution of point defects in irradiated binary semiconductors is considered. This instability arises due to elastic interaction of point defects created by radiation. It was shown that the periodical distribution of point defects have to be must developed in some cases. The area of existence and the parameters of this periodical distribution were estimated for GaAs.